# 74HC163; 74HCT163

# Presettable synchronous 4-bit binary counter; synchronous reset

Rev. 4 — 28 December 2015

**Product data sheet** 

### 1. General description

The 74HC163; 74HCT163 is a synchronous presettable binary counter with an internal look-head carry. Synchronous operation is provided by having all flip-flops clocked simultaneously on the positive-going edge of the clock (CP). The outputs (Q0 to Q3) of the counters may be preset to a HIGH or LOW. A LOW at the parallel enable input (PE) disables the counting action. It causes the data at the data inputs (D0 to D3) to be loaded into the counter on the positive-going edge of the clock. Preset takes place regardless of the levels at count enable inputs (CEP and CET). A LOW at the master reset input (MR) sets Q0 to Q3 LOW after the next positive-going transition on the clock input (CP). This action occurs regardless of the levels at input pins PE, CET and CEP. This synchronous reset feature enables the designer to modify the maximum count with only one external NAND gate. The look-ahead carry simplifies serial cascading of the counters. Both CEP and CET must be HIGH to count. The CET input is fed forward to enable the terminal count output (TC). The TC output thus enabled will produce a HIGH output pulse of a duration approximately equal to a HIGH output of Q0. This pulse can be used to enable the next cascaded stage. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V<sub>CC</sub>.

The CP to TC propagation delay and CEP to CP set-up time determine the maximum clock frequency for the cascaded counters according to the following formula:

$$f_{max} = \frac{1}{t_{P(max)}(CPtoTC) + t_{SU}(CEPtoCP)}$$

### 2. Features and benefits

- Complies with JEDEC standard no. 7A
- Input levels:
  - ◆ For 74HC163: CMOS level
  - For 74HCT163: TTL level
- Synchronous counting and loading
- 2 count enable inputs for n-bit cascading
- Synchronous reset
- Positive-edge triggered clock
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

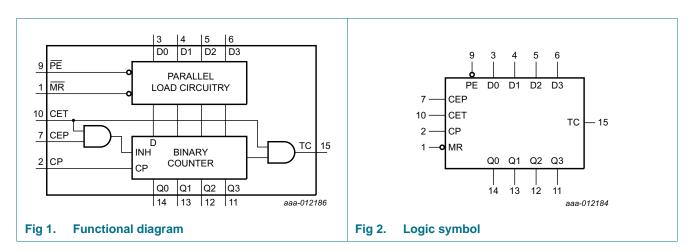


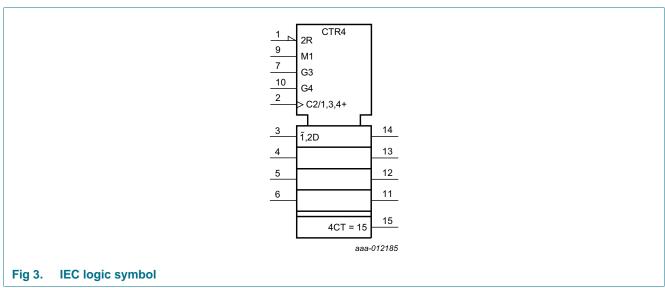
# 3. Ordering information

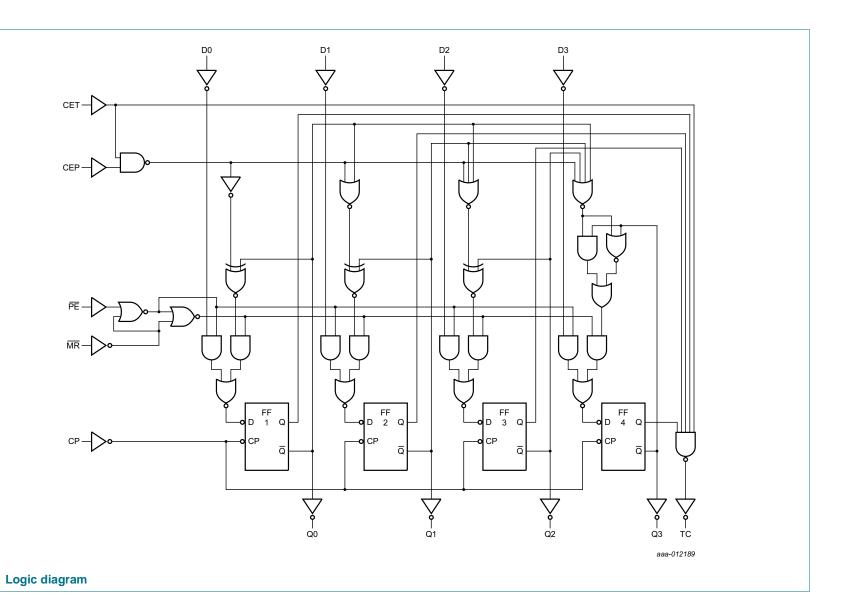
Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74HC163D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads;	SOT109-1					
74HCT163D			body width 3.9 mm						
74HC163DB	-40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads;	SOT338-1					
74HCT163DB			body width 5.3 mm						
74HC163PW	−40 °C to +125 °C	TSSOP16	process and comment processes, to testing,						
74HCT163PW			body width 4.4 mm						

# 4. Functional diagram

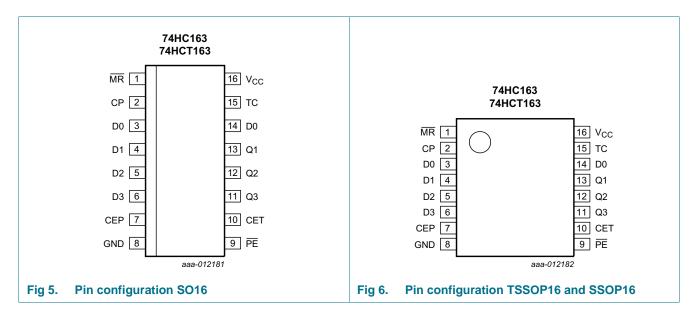






# 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

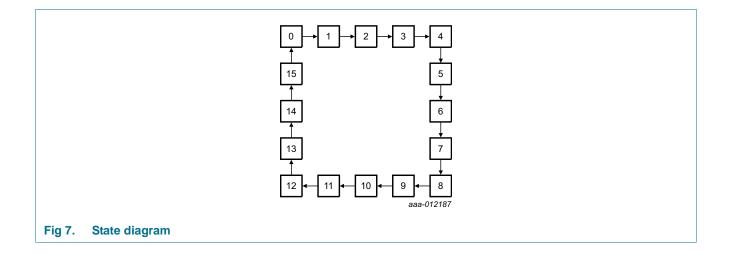
Symbol	Pin	Description
MR	1	synchronous master reset (active LOW)
СР	2	clock input (LOW-to-HIGH, edge triggered)
D0, D1, D2, D3	3, 4, 5, 6	data input
CEP	7	count enable input
GND	8	ground (0 V)
PE	9	parallel enable input (active LOW)
CET	10	count enable carry input
Q0, Q1, Q2, Q3	14, 13, 12, 11	flip-flop output
TC	15	terminal count output
V <sub>CC</sub>	16	supply voltage

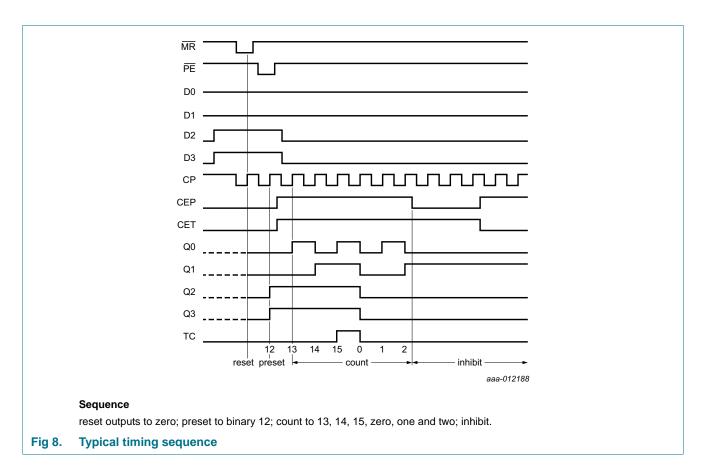
## 6. Functional description

Table 3. Function table[1]

Operating mode	Inputs	Inputs									
	MR	CP	CEP	CET	PE	Dn	Qn	TC			
Reset (clear)	I	<b>↑</b>	Х	Х	Х	Х	L	L			
Parallel load	h	1	Х	Х	I	I	L	L			
	h	1	Х	Х	I	h	Н	L			
Count	h	1	h	h	h	Х	count				
Hold (do nothing)	h	Х	I	Х	h	Х	qn	L			
	h	Х	Х	I	h	Х	qn	L			

- [1] The TC output is HIGH when CET is HIGH and the counter is at terminal count (HHHH);
  - H = HIGH voltage level;
  - h = HIGH voltage level one set-up time prior to the LOW-to-HIGH CP transition;
  - L = LOW voltage level;
  - I = LOW voltage level one set-up time prior to the LOW-to-HIGH CP transition;
  - q = lower case letters indicate the state of the referenced output one set-up time prior to the
  - LOW-to-HIGH CP transition;
  - X = don't care;
  - ↑ = LOW-to-HIGH clock transition.





## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CC}$	supply voltage			-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } V_{CC} + 0.5 \text{ V}$		-	±25	mA
I <sub>CC</sub>	supply current			-	50	mA
I <sub>GND</sub>	ground current			-50	-	mA
T <sub>stg</sub>	storage temperature			<b>−65</b>	+150	°C
P <sub>tot</sub>	total power dissipation	SO16 package	<u>[1]</u>	-	500	mW
		(T)SSOP16 package	<u>[1]</u>	-	500	mW

<sup>[1]</sup> For SO16 packages: above 70 °C the value of  $P_{tot}$  derates linearly at 8 mW/K. For (T)SSOP16 packages: above 60 °C the value of  $P_{tot}$  derates linearly at 5.5 mW/K.

# 8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC163			7	3	Unit	
			Min	Тур	Max	Min	Тур	Max	_
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.0 V	-	-	625	-	-	-	ns/V
		V <sub>CC</sub> = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V <sub>CC</sub> = 6.0 V	-	-	83	-	-	-	ns/V

### 9. Static characteristics

#### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC163	3									
$V_{IH}$	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
$V_{IL}$	LOW-level	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0$ ; $V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2$ ; $V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μА
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80.0	-	160.0	μА

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT16	63							I		
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80.0	-	160.0	μΑ
Δl <sub>CC</sub>	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$ ; other inputs at $V_{CC}$ or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V; $I_O = 0 \text{ A}$								
		pin MR	-	95	342	-	427.5	-	465.5	μΑ
		pin CP	-	110	396	-	495	-	539	μΑ
		pin CEP and Dn	-	25	90	-	112.5	-	122.5	μΑ
		pin CET	-	75	270	-	337.5	-	367.5	μΑ
		pin PE	-	30	108	-	135	-	147	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

# 10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit see Figure 14.

Symbol	Parameter	Conditions		25 °C		-40 °C to	+85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC16	3								_	
t <sub>pd</sub>	propagation	CP to Qn; see Figure 9								
	delay	V <sub>CC</sub> = 2.0 V	-	55	185	-	230	-	280	ns
		V <sub>CC</sub> = 4.5 V	-	20	37	-	46	-	56	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	17	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	16	31	-	39	-	48	ns
		CP to TC; see Figure 9								
		V <sub>CC</sub> = 2.0 V	-	69	215	-	270	-	320	ns
		V <sub>CC</sub> = 4.5 V	-	25	43	-	54	-	65	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	21	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	20	37	-	46	-	55	ns
		CET to TC; see Figure 10								
		V <sub>CC</sub> = 2.0 V	-	36	120	-	150	-	180	ns
		V <sub>CC</sub> = 4.5 V	-	13	24	-	30	-	36	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	11	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	10	20	-	26	-	31	ns
t <sub>t</sub>	transition	see Figure 9 and Figure 10 [2]								
	time	V <sub>CC</sub> = 2.0 V	-	19	75	-	95	-	110	ns
		V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns
		V <sub>CC</sub> = 6.0 V	-	6	13	-	16	-	19	ns
t <sub>W</sub>	pulse width	CP; HIGH or LOW; see Figure 9								
		V <sub>CC</sub> = 2.0 V	80	17	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	6	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	5	-	17	-	20	-	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit see Figure 14.

Symbol	Parameter	Conditions		25 °C		-40 °C to ⋅	+85 °C	–40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
t <sub>su</sub>	set-up time	MR, Dn to CP; see Figure 11 and Figure 12								
		V <sub>CC</sub> = 2.0 V	80	17	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	6	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	5	-	17	-	20	-	ns
		PE to CP; see Figure 11								
		V <sub>CC</sub> = 2.0 V	80	22	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	8	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	6	-	17	-	20	-	ns
		CEP, CET to CP; see Figure 13								
		V <sub>CC</sub> = 2.0 V	175	58	-	220	-	265	-	ns
		V <sub>CC</sub> = 4.5 V	35	21	-	44	-	53	-	ns
		V <sub>CC</sub> = 6.0 V	30	17	-	37	-	45	-	ns
t <sub>h</sub>	hold time	Dn, PE, CEP, CET, MR to CP; see Figure 11, Figure 12 and Figure 13								
		V <sub>CC</sub> = 2.0 V	0	-14	-	0	-	0	-	ns
		V <sub>CC</sub> = 4.5 V	0	<b>–</b> 5	-	0	-	0	-	ns
		V <sub>CC</sub> = 6.0 V	0	-4	-	0		0	-	ns
f <sub>max</sub>	maximum	CP; see Figure 9								
	frequency	V <sub>CC</sub> = 2.0 V	5	15	-	4	-	4	-	MHz
		V <sub>CC</sub> = 4.5 V	27	46	-	22	-	18	-	MHz
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	51	-	-	-	-	-	MHz
		V <sub>CC</sub> = 6.0 V	32	55	-	26	-	21	-	MHz
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}; V_{CC} = 5 \text{ V};$ $f_i = 1 \text{ MHz}$	-	33	-	-	-	-	-	pF

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit see Figure 14.

Symbol	Parameter	Conditions		25 °C		–40 °C to	+85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HCT1	93					1				
t <sub>pd</sub>	propagation	CP to Qn; see Figure 9	1							
	delay	V <sub>CC</sub> = 4.5 V	-	23	39	-	49	-	59	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	20	-	-	-	-	-	ns
		CP to TC; see Figure 9								
		V <sub>CC</sub> = 4.5 V	-	29	49	-	61	-	74	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	25	-	-	-	-	-	ns
		CET to TC; see Figure 10								
		V <sub>CC</sub> = 4.5 V	-	17	32	-	44	-	48	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	14	-	-	-	-	-	ns
t <sub>t</sub>	transition	see Figure 9 and Figure 10	1							
time	V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns	
t <sub>W</sub> pulse wi	pulse width	CP; HIGH or LOW; see Figure 9								
		V <sub>CC</sub> = 4.5 V	20	6	-	25	-	30	-	ns
t <sub>su</sub>	set-up time	MR, Dn to CP; see Figure 11 and Figure 12								
		V <sub>CC</sub> = 4.5 V	20	9	-	25	-	30	-	ns
		PE to CP; see Figure 11								
		V <sub>CC</sub> = 4.5 V	20	11	-	25	-	30	-	ns
		CEP, CET to CP; see Figure 13								
		V <sub>CC</sub> = 4.5 V	40	24	-	50	-	60	-	ns
t <sub>h</sub>	hold time	Dn, PE, CEP, CET, MR to CP; see Figure 11, Figure 12 and Figure 13								
		V <sub>CC</sub> = 4.5 V	0	-5	-	0	-	0	-	ns
f <sub>max</sub>	maximum	CP; see Figure 9								
	frequency	V <sub>CC</sub> = 4.5 V	26	45	-	21	-	17	-	MHz
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	50	-	-	-	-	-	MHz

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V);  $C_L = 50$  pF unless otherwise specified; for test circuit see Figure 14.

Symbol	Parameter	Conditions		25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit	
			М	/lin	Тур	Max	Min	Max	Min	Max	
C <sub>PD</sub>	power dissipation capacitance	$V_{I} = GND \text{ to } V_{CC} - 1.5 \text{ V};$ $V_{CC} = 5 \text{ V}; f_{i} = 1 \text{ MHz}$	]	-	35	-	-	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PHL}$  and  $t_{PLH}$ .
- [2]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

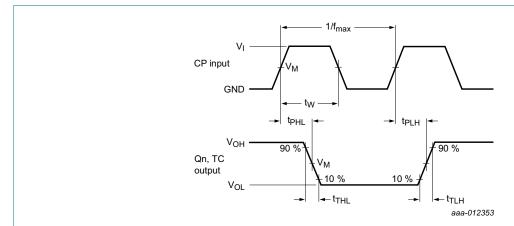
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$ 

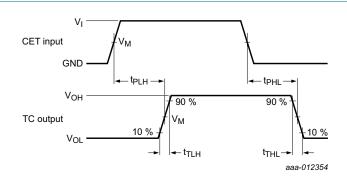
### 11. Waveforms



Measurement points are given in <u>Table 8</u>.

Logic levels  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

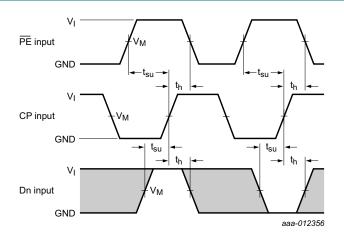
Fig 9. The clock (CP) to outputs (Qn, TC) propagation delays, pulse width, output transition times and maximum frequency



Measurement points are given in Table 8.

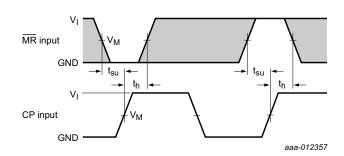
Logic levels  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

Fig 10. The count enable carry input (CET) to terminal count output (TC) propagation delays and output transition times



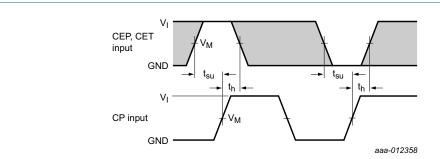
The shaded areas indicate when the input is permitted to change for predictable output performance. Measurement points are given in Table 8.

Fig 11. The data input (Dn) and parallel enable input (PE) set-up and hold times



The shaded areas indicate when the input is permitted to change for predictable output performance. Measurement points are given in <u>Table 8</u>.

Fig 12. The master reset (MR) set-up and hold times

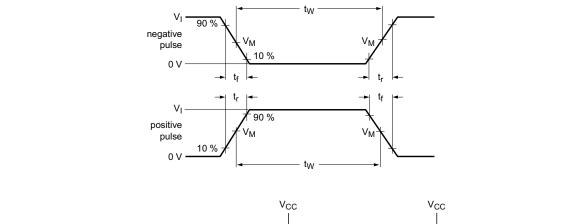


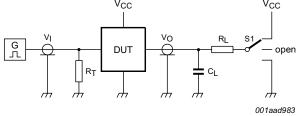
The shaded areas indicate when the input is permitted to change for predictable output performance. Measurement points are given in Table 8.

Fig 13. The count enable input (CEP) and count enable carry input (CET) set-up and hold times

Table 8. Measurement points

Туре	Input	Output	
	V <sub>M</sub>	V <sub>I</sub>	V <sub>M</sub>
74HC163	$0.5 \times V_{CC}$	GND to V <sub>CC</sub>	$0.5 \times V_{CC}$
74HCT163	1.3 V	GND to 3 V	1.3 V





Test data is given in Table 9.

Test circuit definitions:

 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator

 $C_L$  = Load capacitance including jig and probe capacitance

R<sub>L</sub> = Load resistance.

S1 = Test selection switch

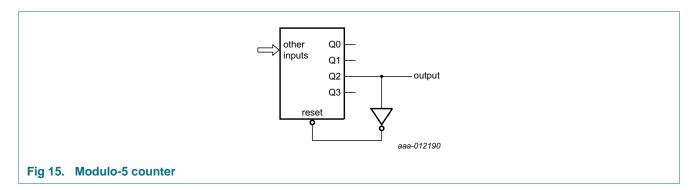
Fig 14. Test circuit for measuring switching times

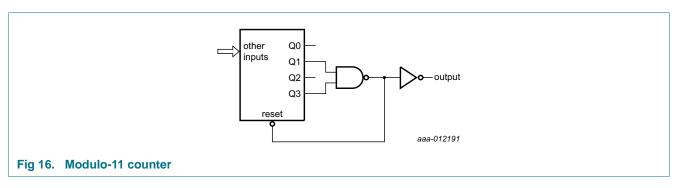
Table 9. Test data

Туре	Input		Load	S1 position	
	V <sub>I</sub>	t <sub>r</sub> , t <sub>f</sub>	CL	R <sub>L</sub>	t <sub>PHL</sub> , t <sub>PLH</sub>
74HC163	V <sub>CC</sub>	6 ns	15 pF, 50 pF	1 kΩ	open
74HCT163	3 V	6 ns	15 pF, 50 pF	1 kΩ	open

# 12. Application information

The 74HC163; 74HCT63 facilitate designing counters of any modulus with minimal external logic. The output is glitch-free due to the synchronous reset.

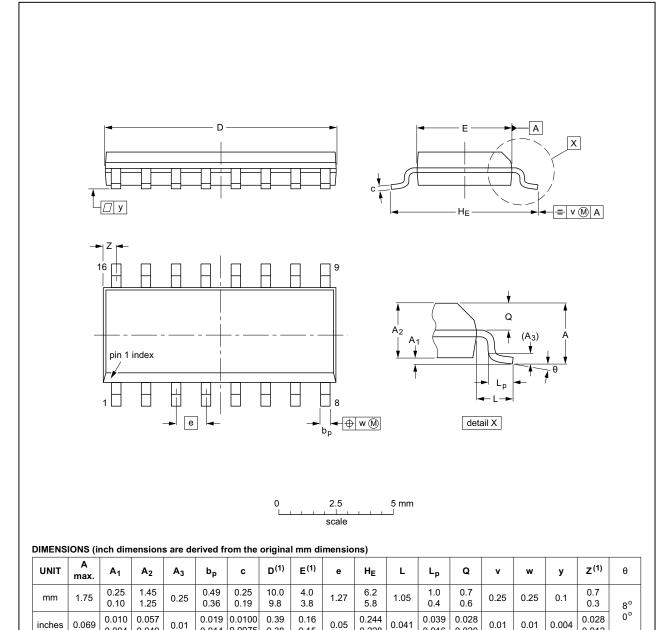




## 13. Package outline

### SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



#### inches

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

0.014 0.0075

0.38

0.15

OUTLINE		REFER	RENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC JEDEC		JEITA		PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				<del>99-12-27</del> 03-02-19	

0.016

0.020

Fig 17. Package outline SOT109-1 (SO16)

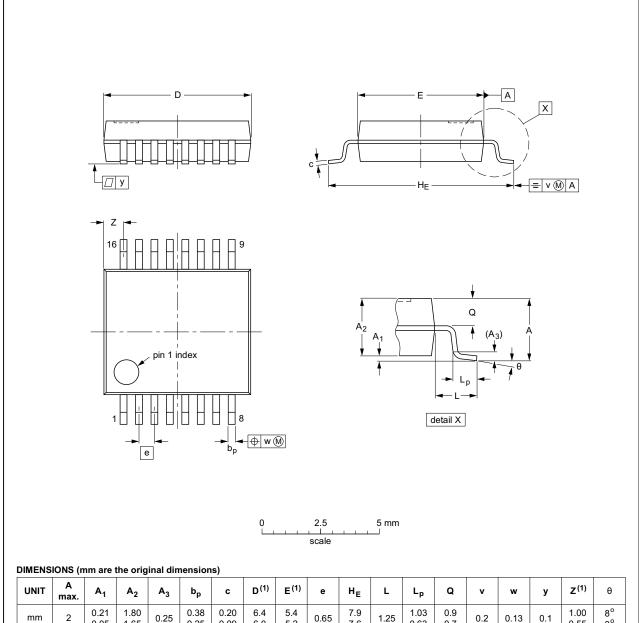
0.004

0.049

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SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	<b>A</b> <sub>3</sub>	b <sub>p</sub>	C	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	٧	w	у	Z <sup>(1)</sup>	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC JEDEC JEITA			PROJECTION	ISSUE DATE	
SOT338-1		MO-150			<del>99-12-27</del> 03-02-19	

Fig 18. Package outline SOT338-1 (SSOP16)

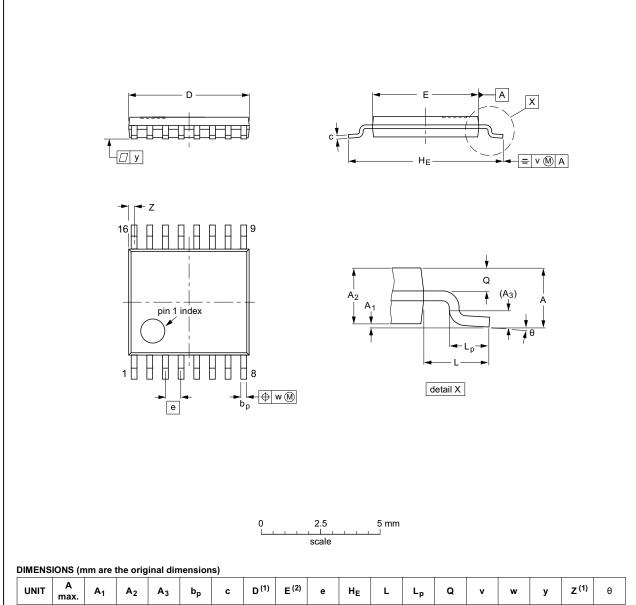
74HC\_HCT163

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



UNI	IT	A max.	<b>A</b> <sub>1</sub>	A <sub>2</sub>	<b>A</b> <sub>3</sub>	bp	С	D <sup>(1)</sup>	E (2)	е	HE	L	Lp	Q	٧	w	у	Z <sup>(1)</sup>	θ
mn	n	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC JEITA		PROJECTION	ISSUE DATE	
SOT403-1		MO-153			<del>99-12-27</del> 03-02-18	

Fig 19. Package outline SOT403-1 (TSSOP16)

74HC\_HCT163

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### 14. Abbreviations

#### Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

# 15. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74HC_HCT163 v.4	20151228	Product data sheet	-	74HC_HCT163 v.3	
Modifications:	Type numbers	3 74HC163N and 74HCT163N	(SOT38-4) removed	d.	
74HC_HCT163 v.3	20140602	Product data sheet	-	74HC_HCT163_CNV v.2	
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>				
	<ul> <li>Legal texts ha</li> </ul>	ive been adapted to the new c	ompany name where	e appropriate.	
74HC_HCT163_CNV v.2	19930927	Product specification	-	-	

### 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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74HC\_HCT163

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### 18. Contents

1	General description
2	Features and benefits
3	Ordering information
4	Functional diagram
5	Pinning information 4
5.1	Pinning
5.2	Pin description
6	Functional description 5
7	Limiting values 6
8	Recommended operating conditions 7
9	Static characteristics 7
10	Dynamic characteristics
11	Waveforms
12	Application information
13	Package outline
14	Abbreviations
15	Revision history
16	Legal information
16.1	Data sheet status 21
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks22
17	Contact information 22
18	Contents 23

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